



40V Dual N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

30 A

Features

- R_{DS(ON)}, V_{GS}@10V, I_D@12A<12mΩ
- $R_{DS(ON)}$, V_{GS} @4.5V, I_{D} @8A<16m Ω
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0035 ounces, 0.092 grams

DFN5060B-8L D1 D1 D2 D2 8 77 6 5 S1 G1 S2 G2

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	l _D	30		
	T _C =100°C		19	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	100	ļ	
Power Dissipation	T _C =25°C	Po	23.8	147	
	T _C =100°C		11.9	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	8.6	Α	
	T _A =70°C		7		
Power Dissipation	T _A =25°C	Po	2.0	W	
	T _A =70°C		1.4		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	62	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	6.3	°C/W	
	Junction to Ambient	$R_{\theta JA}$	73.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.7	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_D =12A	-	10	12	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =4.5V, I_D =8A	-	13	16	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =40V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V _{DS} =20V, I _D =10A, V _{GS} =4.5V (Note 2,3)	-	10	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Input Capacitance	Ciss	V _{DS} =20V, V _{GS} =0V,	-	1040	-	pF
Output Capacitance	Coss		-	117	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	84	-	
Turn-On Delay Time	td _(on)	$\begin{array}{c} V_{DS}{=}20V,\ I_{D}{=}1A,\\ V_{GS}{=}10V,\ R_{G}{=}6\Omega\\ \text{(Note 2,3)} \end{array}$	-	9.4	-	
Turn-On Rise Time	t _r		-	19	-	ns
Turn-Off Delay Time	td _(off)		-	66	-	
Turn-Off Fall Time	t _f		-	67	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					20	_
Diode Forward Current	I _S		-	-	30	Α
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.7	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =35A, V_{DD} =25V, V_{GS} =10V, Starting T_{J} =25 $^{\circ}$ C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

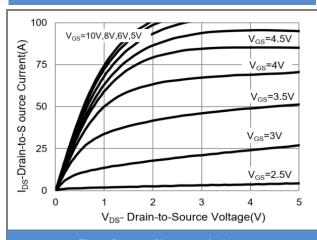


Fig.1 Output Characteristics

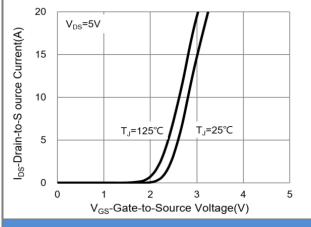


Fig.2 Transfer Characteristics

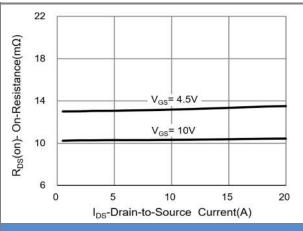


Fig.3 On-Resistance vs. Drain Current

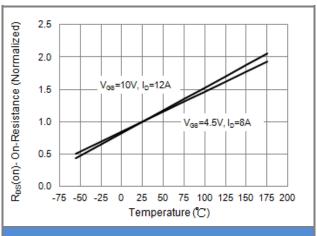
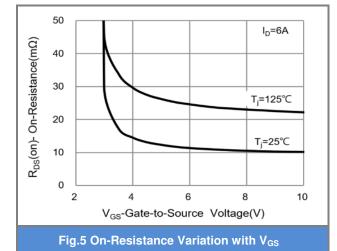


Fig.4 On-Resistance vs. Junction temperature





0.6

T_j=25°C



T_i=125°C

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10

1

0.1

0.01

I_{SD}-Source to Drain Current(A)





TYPICAL CHARACTERISTIC CURVES

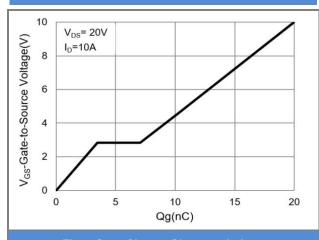


Fig.7 Gate-Charge Characteristics

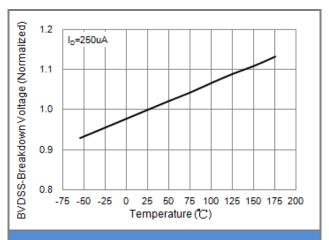


Fig.8 Breakdown Voltage Variation vs. Temperature

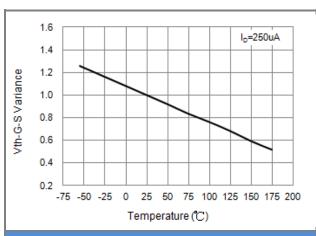


Fig.9 Threshold Voltage Variation with Temperature

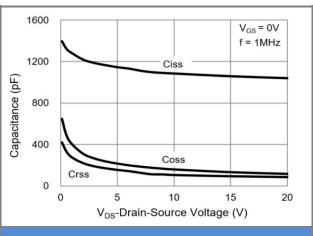


Fig.10 Capacitance vs. Drain-Source Voltage

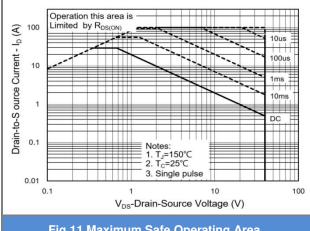


Fig.11 Maximum Safe Operating Area

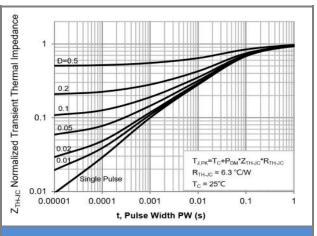


Fig.12 Normalized Transient Thermal Impedance

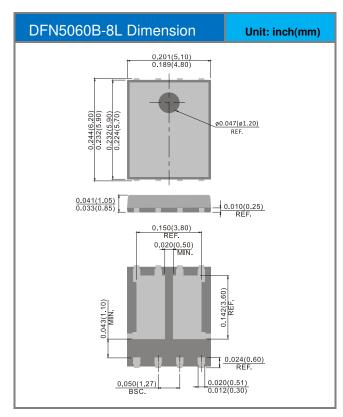


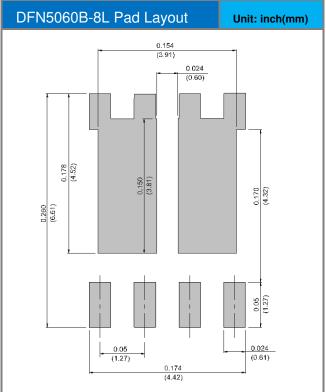


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5848-AU_R2_000A1	DFN5060B-8L	3000pcs / 13" reel	Q5848	Halogen free	

Packaging Information & Mounting Pad Layout









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